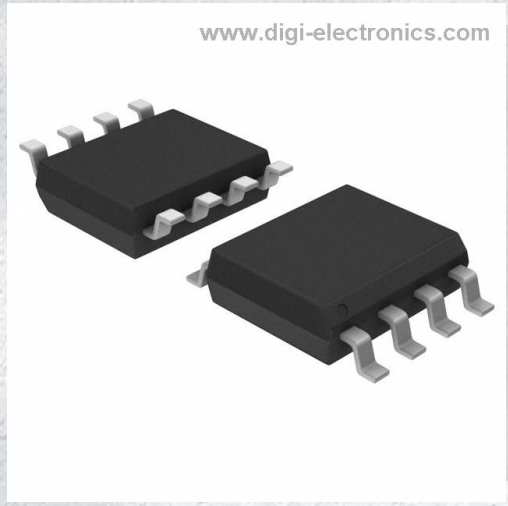
TC6215TG-G Datasheet



DiGi Electronics Part Number	TC6215TG-G-DG
Manufacturer	Microchip Technology
Manufacturer Product Number	TC6215TG-G
Description	MOSFET N/P-CH 150V 8SOIC
Detailed Description	Mosfet Array 150V Surface Mount 8-SOIC

https://www.DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
TC6215TG-G	Microchip Technology
Series:	Product Status:
-	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	N and P-Channel
FET Feature:	Drain to Source Voltage (Vdss):
-	150V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
-	4Ohm @ 2A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 1mA	-
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
120pF @ 25V	-
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	8-SOIC
Base Product Number:	
TC6215	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Supertex inc. **TC6215**

N- and P-Channel Enhancement-Mode Dual MOSFET

Features

- Back to back gate-source Zener diodes
- Guaranteed $R_{DS(ON)}$ at 4.0V gate drive
- Low threshold
- Low on-resistance
- Independent N- and P-channels
- Electrically isolated N- and P-channels
- Low input capacitance
- Fast switching speeds
- Free from secondary breakdowns
- Low input and output leakage

Applications

- High voltage pulsers
- Amplifiers
- Buffers
- Piezoelectric transducer drivers
- General purpose line drivers
- Logic level interfaces

General Description

The Supertex TC6215 consists of high voltage, low threshold N-channel and P-channel MOSFETs in an 8-Lead SOIC (TG) package. Both MOSFETs have integrated back to back gate-source Zener diode clamps and guaranteed $R_{DS(ON)}$ ratings down to 4.0V gate drive allowing them to be driven directly with standard 5.0V CMOS logic.

These low threshold enhancement-mode (normally-off) transistors utilize an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV_{DSS}/BV_{DGS}		$R_{DS(ON)}$ (Max)	
	8-Lead SOIC *4.90x3.90mm body 1.75mm height (max) 1.27mm pitch*	N-Channel (V)	P-Channel (V)	N-Channel (Ω)	P-Channel (Ω)
TC6215	TC6215TG-G	150	-150	4.0	7.0

-G indicates package is RoHS compliant ('Green')

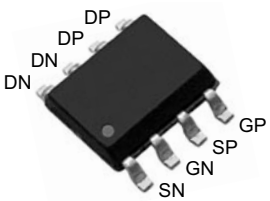
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to + 150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

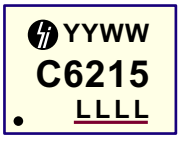
* *Distance of 1.6mm from case for 10 seconds.*

Pin Configuration



8-Lead SOIC (TG)
(top view)

Product Marking



YY = Year Sealed
WW = Week Sealed
L = Lot Number
_____ = "Green" Packaging

Package may or may not include the following marks: Si or

8-Lead SOIC (TG)

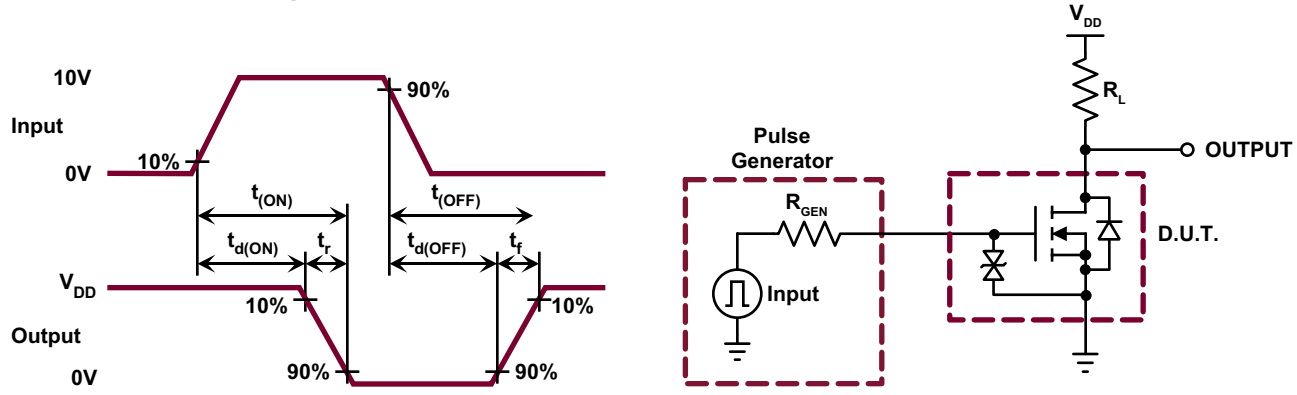
N-Channel Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	150	-	-	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate threshold voltage	1.0	-	2.0	V	V_{GS} = V_{DS}, I_D =1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	-4.5	mV/°C	V_{GS} = V_{DS}, I_D = 1.0mA
VZ_{GS}	Gate-source back to back Zener voltage	±14	-	±25	V	I_{GS} = ±1.0mA
I_{DSS}	Zero gate voltage drain current	-	-	5.0	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	-	2.0	-	A	V_{GS} = 4.5V, V_{DS} = 25V
		-	3.8	-		V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	4.0	Ω	V_{GS} = 4.0V, I_D = 0.5A
		-	-	5.0		V_{GS} = 5.0V, I_D = 2.0A
		-	-	4.0		V_{GS} = 10V, I_D = 2.0A
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.0	%/°C	V_{GS} = 5.0V, I_D = 2.0A
G_{FS}	Forward transconductance	560	-	-	mmho	V_{DS} = 10V, I_D = 0.5A
C_{ISS}	Input capacitance	-	120	-	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	33	-		
C_{RSS}	Reverse transfer capacitance	-	11	-		
$t_{d(ON)}$	Turn-on delay time	-	2.5	-	ns	V_{DD} = 25V, I_D = 1.0A, R_{GEN} = 25Ω
t_r	Rise time	-	2.3	-		
$t_{d(OFF)}$	Turn-off delay time	-	17.2	-		
t_f	Fall time	-	11.3	-		
V_{SD}	Diode forward voltage drop	-	-	1.4	V	V_{GS} = 0V, I_{SD} = 0.5A
t_{rr}	Reverse recovery time	-	90	-	ns	V_{GS} = 0V, I_{SD} = 0.5A

Notes:

1. *All DC parameters 100% tested at 25°C unless otherwise stated. (Pulsed test: 300µs pulse at 2% duty cycle.)*
2. *All AC parameters sample tested.*

N-Channel Switching Waveforms and Test Circuit



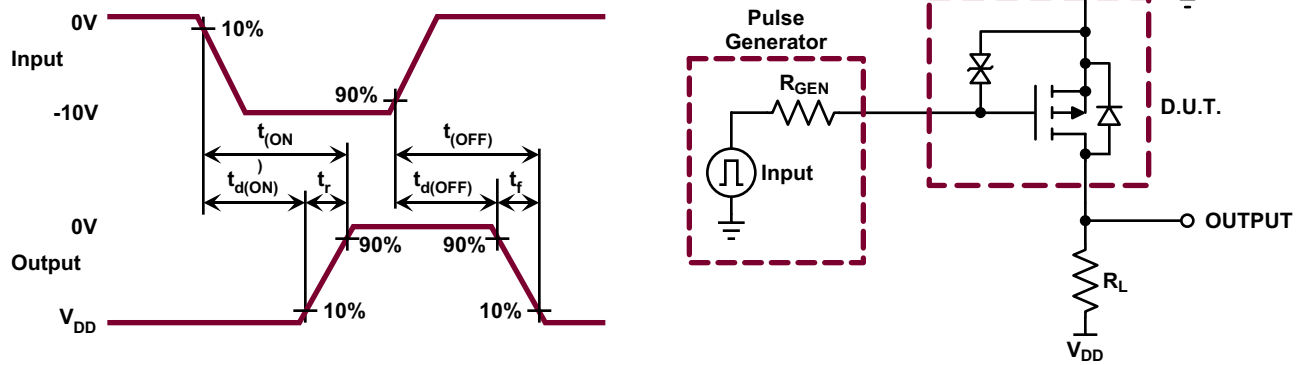
P-Channel Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-150	-	-	V	V_{GS} = 0V, I_D = -1.0mA
$V_{GS(th)}$	Gate threshold voltage	-1.0	-	-2.0	V	V_{GS} = V_{DS}, I_D =-1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	4.5	mV/°C	V_{GS} = V_{DS}, I_D = -1.0mA
VZ_{GS}	Gate-source back to back Zener voltage	±14	-	±25	V	I_{GS} = ±1.0mA
I_{DSS}	Zero gate voltage drain current	-	-	-5.0	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	-1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	-	-1.5	-	A	V_{GS} = -4.5V, V_{DS} = -25V
		-	-3.0	-		V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	7.5	Ω	V_{GS} = -4.0V, I_D = -0.25A
		-	-	9.0		V_{GS} = -5.0V, I_D = -1.0A
		-	-	7.0		V_{GS} = -10V, I_D = -2.0A
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.0	%/°C	V_{GS} = -5.0V, I_D = -0.25A
G_{FS}	Forward transconductance	290	-	-	mmho	V_{DS} = -10V, I_D = -0.25A
C_{ISS}	Input capacitance	-	127	-	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	29	-		
C_{RSS}	Reverse transfer capacitance	-	9.0	-		
$t_{d(ON)}$	Turn-on delay time	-	2.4	-	ns	V_{DD} = -25V, I_D = -1.0A, R_{GEN} = 25Ω
t_r	Rise time	-	2.3	-		
$t_{d(OFF)}$	Turn-off delay time	-	16.2	-		
t_f	Fall time	-	11.1	-		
V_{SD}	Diode forward voltage drop	-	-	-1.4	V	V_{GS} = 0V, I_{SD} = -0.25A
t_{rr}	Reverse recovery time	-	80	-	ns	V_{GS} = 0V, I_{SD} = -0.25A

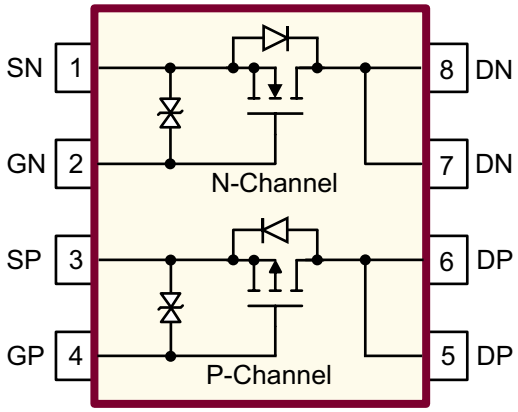
Notes:

1. *All DC parameters 100% tested at 25°C unless otherwise stated. (Pulsed test: 300µs pulse at 2% duty cycle.)*
2. *All AC parameters sample tested.*

P-Channel Switching Waveforms and Test Circuit



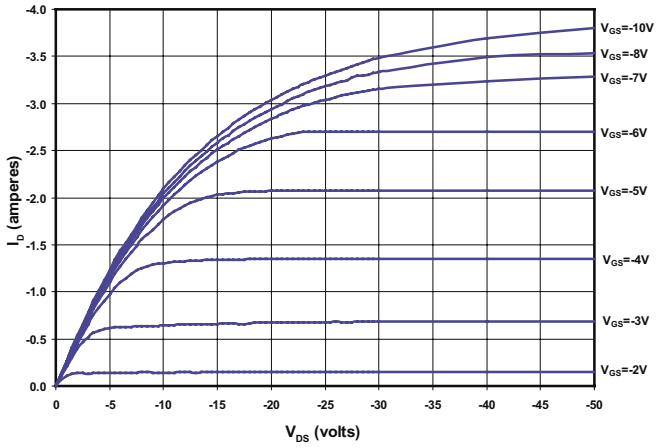
Block Diagram



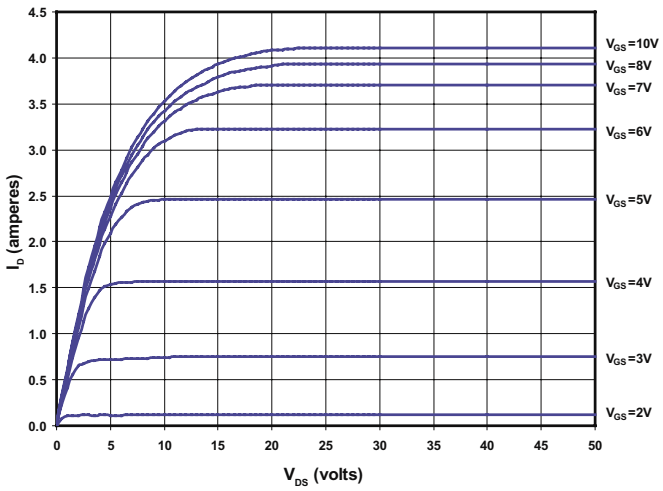
8-Lead SOIC
(top view)

Typical Performance Curves

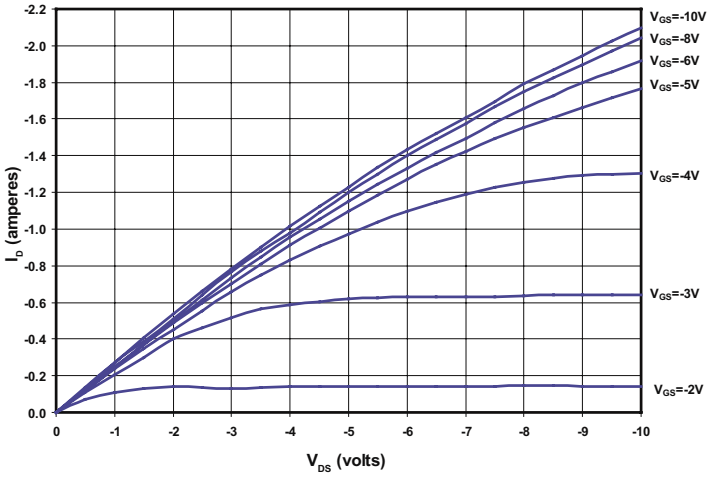
P-Channel Output Characteristics



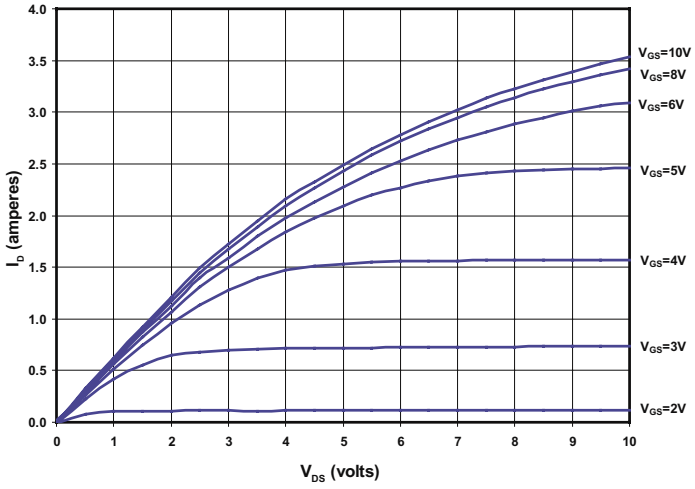
N-Channel Output Characteristics



P-Channel Saturation Characteristics

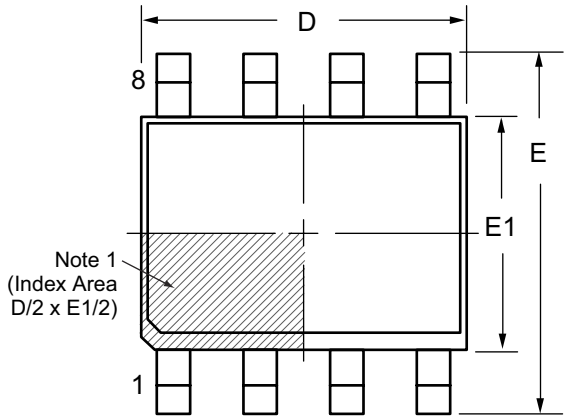


N-Channel Saturation Characteristics

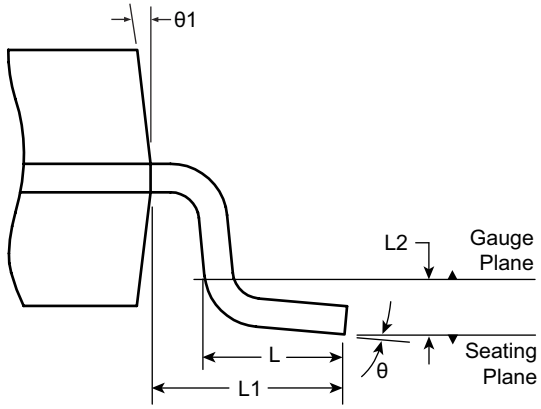


8-Lead SOIC (Narrow Body) Package Outline (TG)

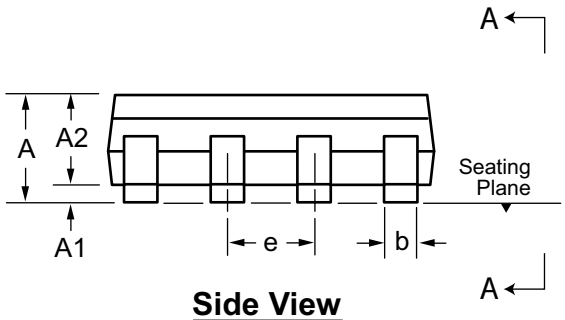
4.90x3.90mm body, 1.75mm height (max), 1.27mm pitch



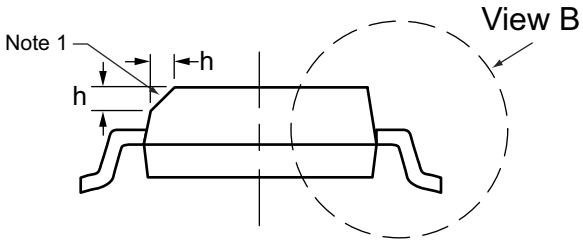
Top View



View B



Side View



View A-A

Note:

1. *This chamfer feature is optional. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.*

Symbol		A	A1	A2	b	D	E	E1	e	h	L	L1	L2	θ	θ1
Dimension (mm)	MIN	1.35*	0.10	1.25	0.31	4.80*	5.80*	3.80*	1.27 BSC	0.25	0.40	1.04 REF	0.25 BSC	0°	5°
	NOM	-	-	-	-	4.90	6.00	3.90		-	-			-	-
	MAX	1.75	0.25	1.65*	0.51	5.00*	6.20*	4.00*		0.50	1.27			8°	15°

JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.

** This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.*

Drawings are not to scale.

Supertex Doc. #: *DSPD-8SOLGTG, Version H101708.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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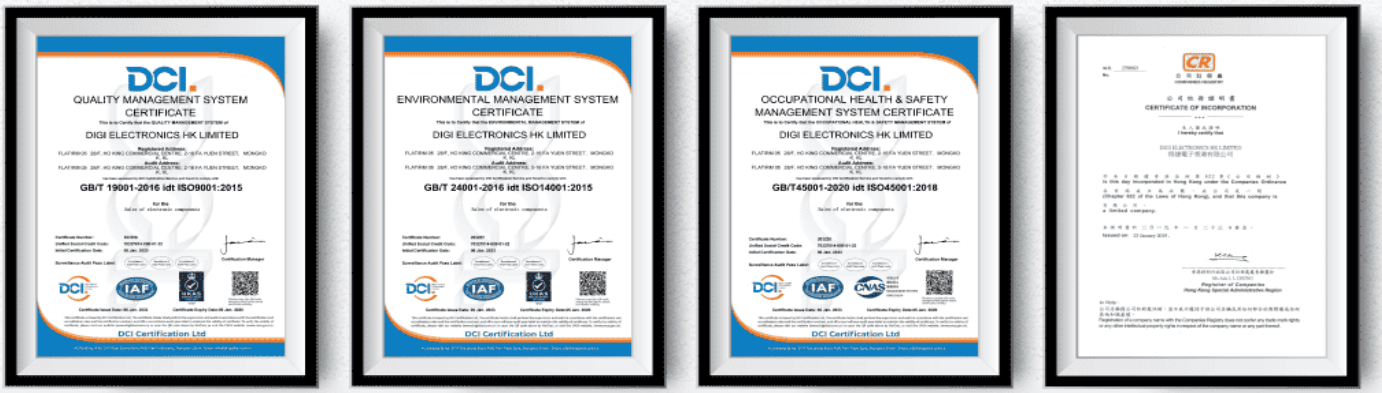

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